

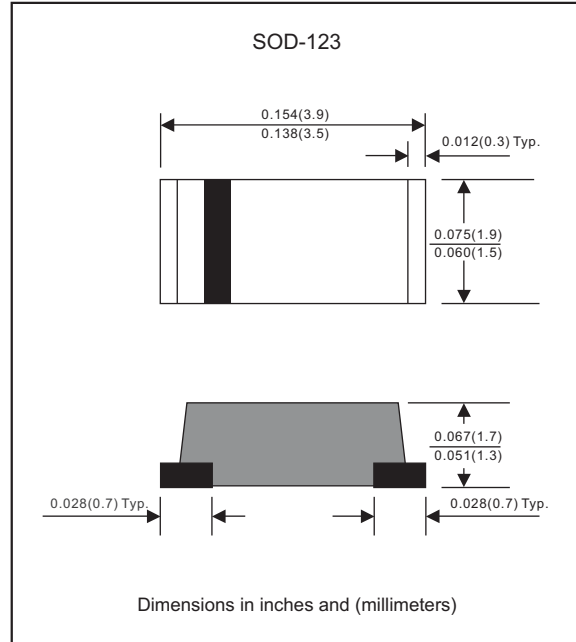
Features

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- Tiny plastic SMD package.
- High current capability.
- Ultrafast recovery time for high efficiency.
- High surge current capability.
- Glass passivated chip junction.
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen free parts, ex. HAS101-M-H.

Mechanical data

- Epoxy : UL94-V0 rated flame retardant
- Case : Molded plastic, SOD-123 / MINI SMA
- Terminals :Plated terminals, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.018 gram

Package outline



Maximum ratings and Electrical Characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.2	I_o			1.0	A
Forward surge current	8.3ms single half sine-wave (JEDEC methode)	I_{FSM}			30	A
Reverse current	$V_R = V_{RRM}$ $T_J = 25^{\circ}\text{C}$	I_R			5.0	μA
	$V_R = V_{RRM}$ $T_J = 125^{\circ}\text{C}$				150	
Diode junction capacitance	f=1MHz and applied 4V DC reverse voltage	C_J		20		pF
Storage temperature		T_{STG}	-65		+175	$^{\circ}\text{C}$

SYMBOLS	V_{RRM}^{*1} (V)	V_{RMS}^{*2} (V)	V_R^{*3} (V)	V_F^{*4} (V)	t_{rr}^{*5} (ns)	Operating temperature $T_J, (^{\circ}\text{C})$
HAS101-M	50	35	50	1.00	50	
HAS102-M	100	70	100			
HAS103-M	200	140	200			
HAS104-M	400	280	400	1.30	75	
HAS105-M	600	420	600			
HAS106-M	800	560	800			
HAS107-M	1000	700	1000			

- *1 Repetitive peak reverse voltage
- *2 RMS voltage
- *3 Continuous reverse voltage
- *4 Maximum forward voltage@ $I_F=1.0\text{A}$
- *5 Maximum Reverse recovery time, note 1

Note 1. Reverse recovery time test condition, $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$

Rating and characteristic curves (HAS101-M THRU HAS107-M)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

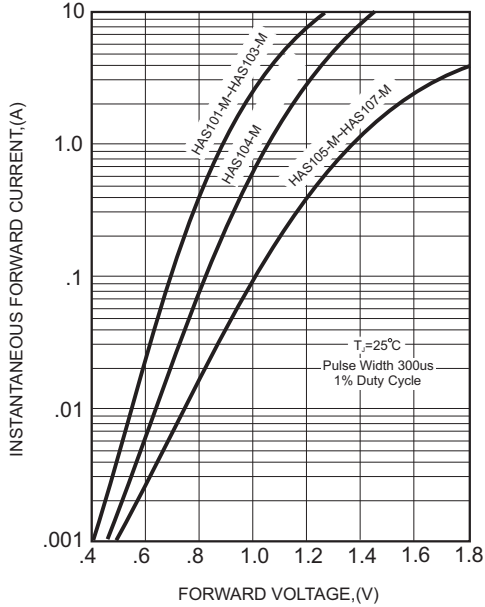


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

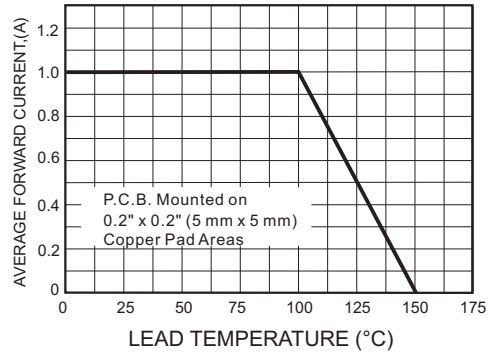


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

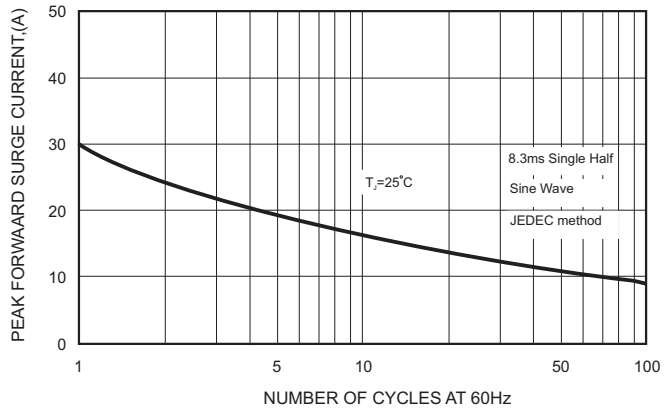
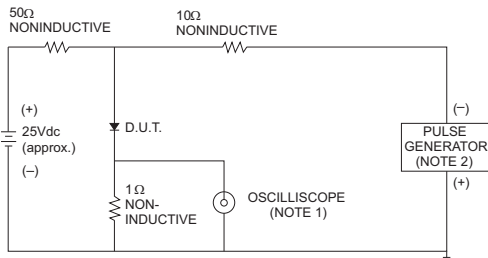


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm, 22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

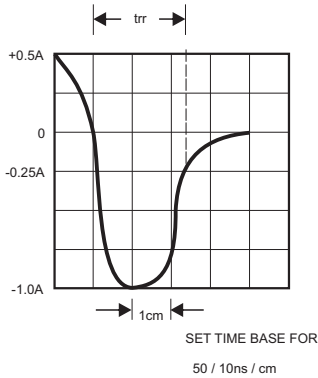
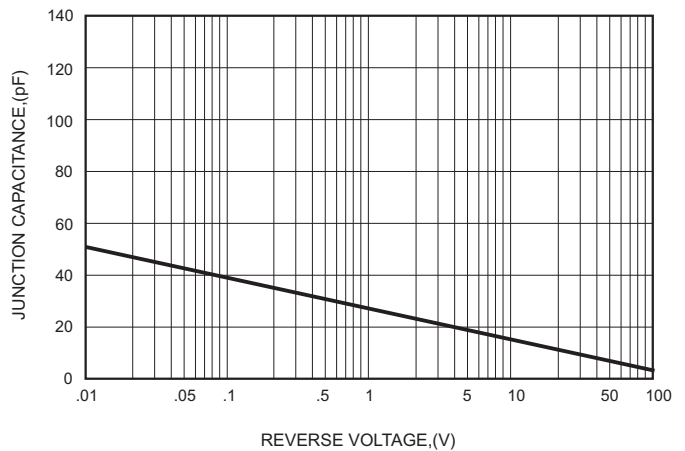




FIG.5-TYPICAL JUNCTION CAPACITANCE



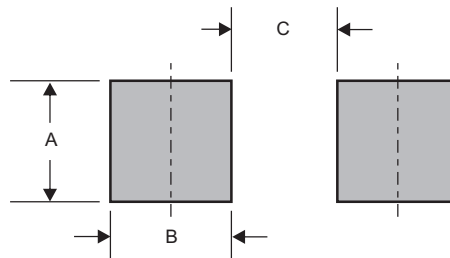
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
HAS101-M	H1
HAS102-M	H2
HAS103-M	H3
HAS104-M	H4
HAS105-M	H5
HAS106-M	H6
HAS107-M	H7

Suggested solder pad layout



Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SOD-123	0.075 (1.90)	0.055 (1.40)	0.075 (1.90)

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